

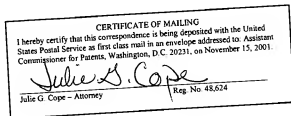


IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of

Applicant : David L. Chapek
Serial No. : 09/605,293
Filed : June 28, 2000
Title : SEMICONDUCTOR DEVICES INCLUDING A LAYER OF
POLYCRYSTALLINE SILICON HAVING A SMOOTH MORPHOLOGY
Docket : MIO 0037 VA
Art Unit : 2811

Assistant Commissioner for Patents
Washington, DC 20231



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TECHNOLOGY CENTER 2800

Sir:

AMENDMENT

This paper is being filed in response to the Office Action mailed on October 2, 2001. Reconsideration is respectfully requested in light of the remarks below.

CLEAN VERSION OF THE AMENDMENTS

(A version of these amendments with markings to show the changes is attached to this paper as a separate appendix.)

IN THE CLAIMS

9. (Amended) A semiconductor device precursor comprising:

a semiconductor substrate;
a layer of silicon dioxide formed on said semiconductor substrate, said layer of silicon dioxide having been doped with hydrogen ions deposited by a plasma source ion implantation process, wherein said layer of silicon dioxide is free of metal contaminants; and
a layer of polycrystalline silicon formed on said layer of silicon dioxide, said layer of polycrystalline silicon having a smooth morphology.

10. (Amended) A field effect transistor comprising: